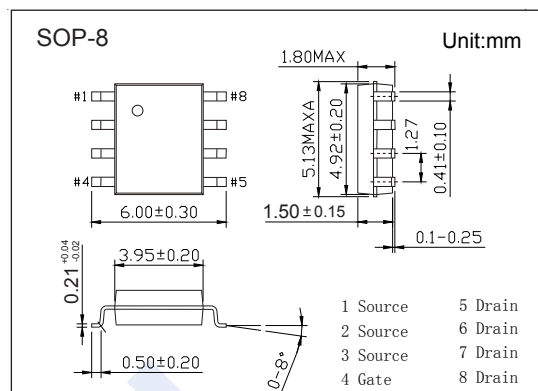
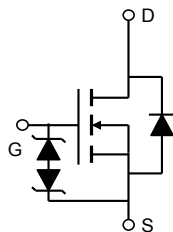


N-Channel MOSFET

AO4498E (KO4498E)

■ Features

- $V_{DS} (V) = 30V$
- $I_D = 18 A (V_{GS} = 10V)$
- $R_{DS(ON)} < 5.8m\Omega (V_{GS} = 10V)$
- $R_{DS(ON)} < 8.5m\Omega (V_{GS} = 4.5V)$
- ESD Rating: 2KV HBM

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	$T_A = 25^\circ C$	I_D	18	A
	$T_A = 70^\circ C$		14	
Pulsed Drain Current		I_{DM}	120	
Power Dissipation	$T_A = 25^\circ C$	P_D	3.1	W
	$T_A = 70^\circ C$		2	
Thermal Resistance.Junction- to-Ambient	$t \leq 10s$	R_{thJA}	40	$^\circ C/W$
	Steady-State		75	
Thermal Resistance.Junction- to-Lead		R_{thJL}	24	
Junction Temperature		T_J	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55 to 150	

N-Channel MOSFET

AO4498E (KO4498E)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 μA, V _{GS} =0V	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _D =30V, V _{GS} =0V			1	μA
		V _D =30V, V _{GS} =0V, T _J =55°C			5	
Gate-Body Leakage Current	I _{GSS}	V _D =0V, V _{GS} =±20V			±10	μA
Gate Threshold Voltage	V _{GS(th)}	V _D =V _{GS} , I _D =250μA	1.3		2.3	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =18A			5.8	mΩ
		V _{GS} =10V, I _D =18A T _J =125°C			8.9	
		V _{GS} =5V, I _D =16A			8.5	
On State Drain Current	I _{D(ON)}	V _{GS} =10V, V _D =5V	120			A
Forward Transconductance	g _{FS}	V _D =5V, I _D =18A		50		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _D =15V, f=1MHz	1840		2760	pF
Output Capacitance	C _{oss}		230		430	
Reverse Transfer Capacitance	C _{rss}		145		340	
Gate Resistance	R _g	V _{GS} =0V, V _D =0V, f=1MHz	0.6		1.9	Ω
Total Gate Charge (10V)	Q _g	V _{GS} =10V, V _D =15V, I _D =18A	34		50	nC
Total Gate Charge (4.5V)			16		24	
Gate Source Charge			5.6		8.4	
Gate Drain Charge			6		14	
Turn-On DelayTime	t _{d(on)}	V _{GS} =10V, V _D =15V, R _L =0.83Ω, R _{GEN} =3Ω		8		ns
Turn-On Rise Time	t _r			10		
Turn-Off DelayTime	t _{d(off)}			33		
Turn-Off Fall Time	t _f			8		
Body Diode Reverse Recovery Time	t _{rr}	I _F = 18A, di/dt= 500A/us	10		15	nC
Body Diode Reverse Recovery Charge	Q _{rr}		22		32	
Maximum Body-Diode Continuous Current	I _S				4	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V			1	V

Note : The static characteristics in Figures 1 to 6 are obtained using <300 us pulses, duty cycle 0.5% max.

■ Marking

Marking	4498E KC****
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N-Channel MOSFET

AO4498E (KO4498E)

Typical Characteristics

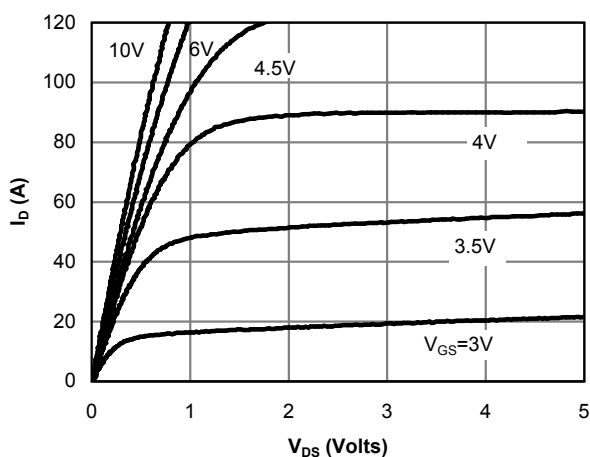


Figure 1: On-Region Characteristics (Note E)

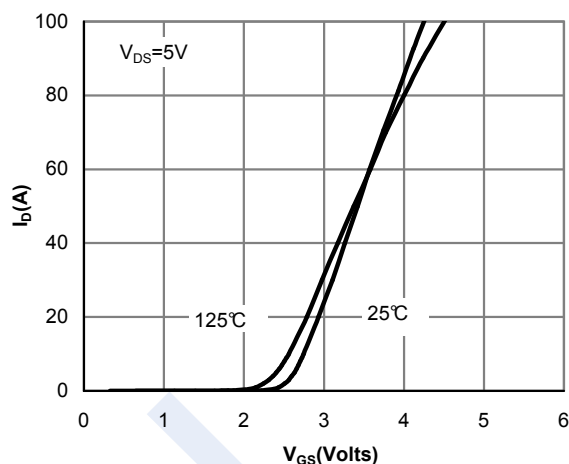


Figure 2: Transfer Characteristics (Note E)

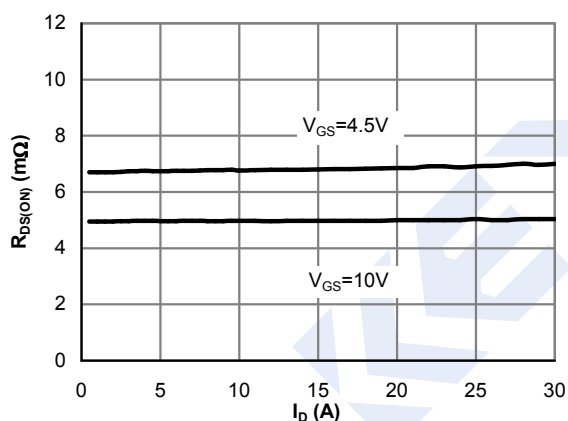


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

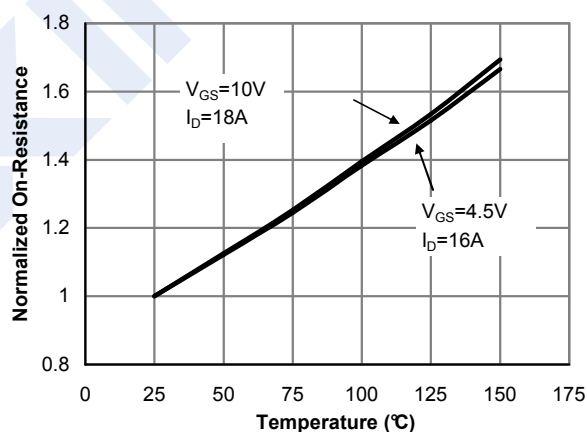


Figure 4: On-Resistance vs. Junction Temperature (Note E)

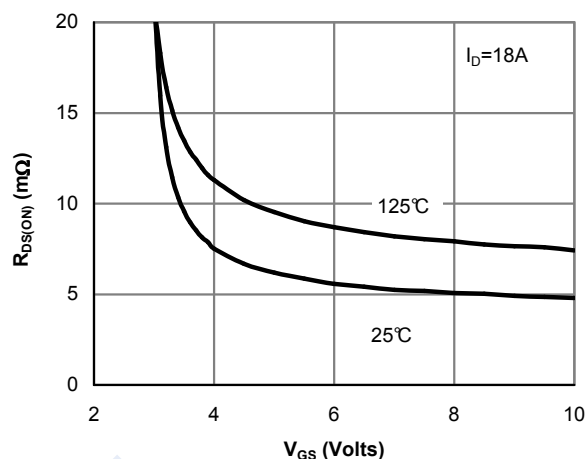


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

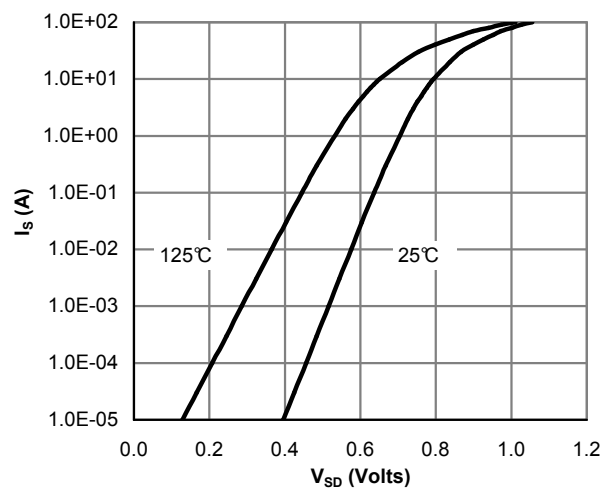


Figure 6: Body-Diode Characteristics (Note E)

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■ Typical Characteristics

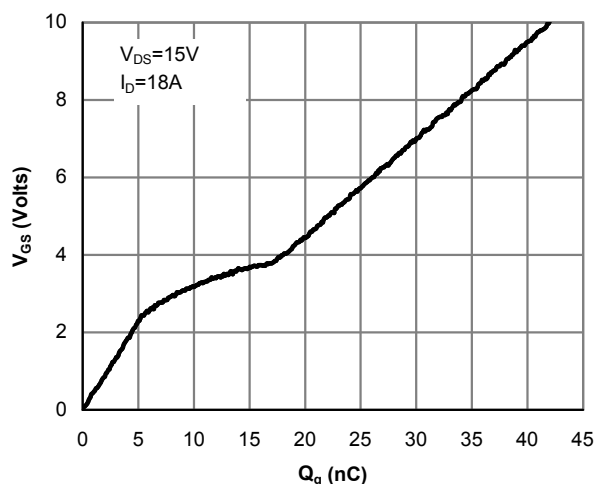


Figure 7: Gate-Charge Characteristics

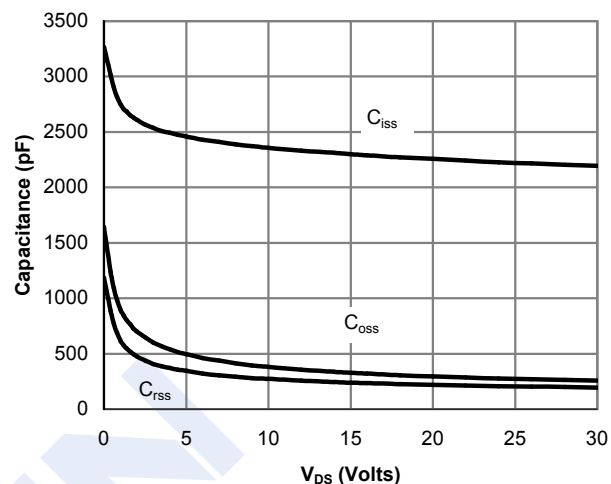


Figure 8: Capacitance Characteristics

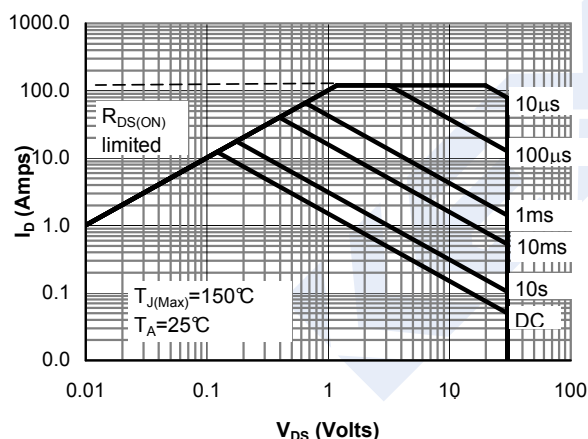


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

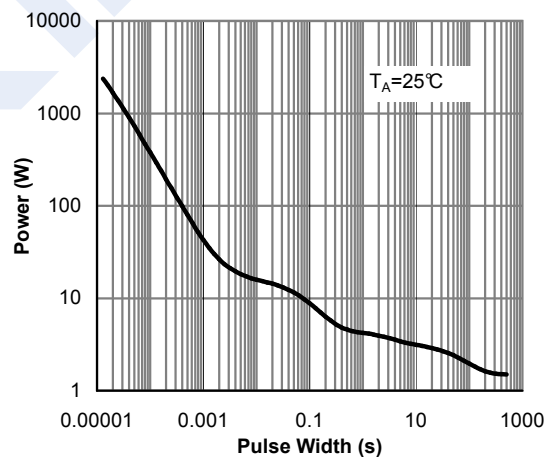


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

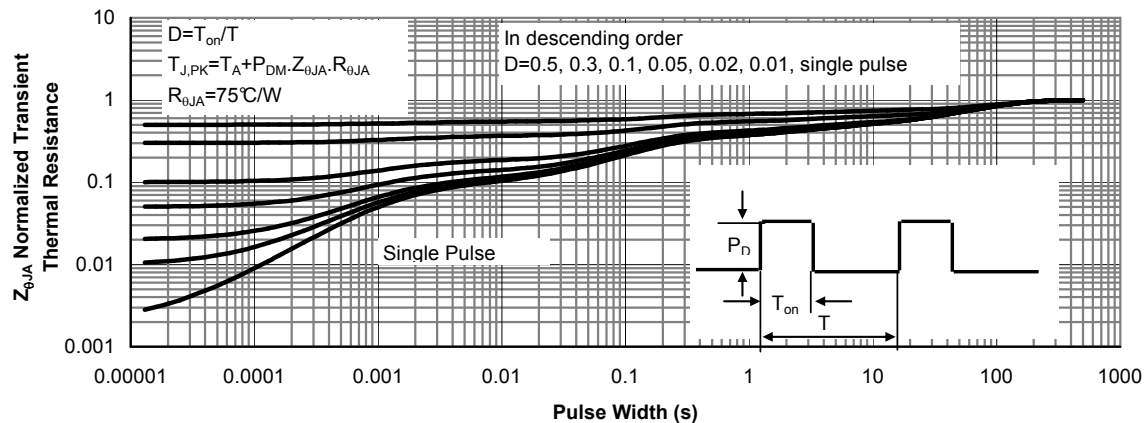


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)